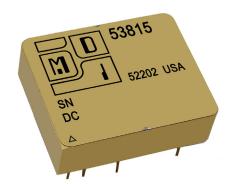
HYBRID SOLID STATE RELAY

Proton Rad Hard 100K + Technology

MODELS 53814/53815



Features:

- High Voltage/Low Resistance
- Single Pole, Single Throw Available in Form A or Form B
- Wide Band Gap Semiconductors for low Besistance
- No SEE LET>82Mev*cm²/mg
- 100K+ Rad Hard TID 100kRads (S and SE Grades)
- TID 45 krads (L and LE Grades)
- Magnetically Coupled Command for fast response
- No Optocoupler, no optocoupler issues
- Selectable Continuous or Mag Latch Function
- Logic Level Drive
- Rugged "Mini" Hermetic Package

Specifications:

Bias Input Voltage 4.7 to 5.3VDC

Bias current 25mA typical, 45mA maximum

Operate pin current 5mA maximum

Input/output and all pins to case isolation 1kV

Power Dissipation 2 watts at maximum rated case temperature

Case temperature range:

Operating -55°C to +85°C (L, S grade) Operating -55°C to +125°C (LE, SE grade)

Storage -65°C to +150°C

Weight: 18 grams typical

To energize the SSR, connect 5VDC bias from pin 1 to bias ground pin 2.

Ground pin 3 to energize the SSR.

Power Dissipation:

Total steady state power dissipation of the model 53815 and 53814 is limited to 2 watts provided the baseplate temperature is limited to the rated temperature.



Model 53815 is a SPST form B (normally closed when de-energized) SSR. Model 53814 is a SPST form A (normally open when de-energized) SSR.

Both types use Wide Bandgap power semiconductors for high performance, are magnetically coupled and can be user configured for continuous or pulse latching.

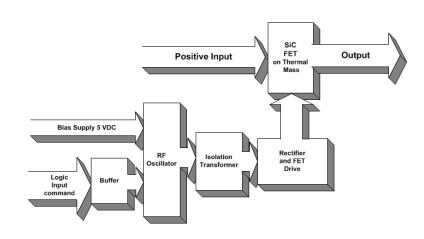
Wide band gap (WBG) semiconductors, such as GaN (Gallium Nitride) and SiC (Silicon Carbide) provide an order of magnitude improvement in SSR voltage drop compared to SSRs using Silicon based power devices.

Also, WBG semiconductors of a given dimension can withstand higher electric fields than Silicon semiconductors, the physical dimensions of these WBG parts are considerably smaller than their Silicon competitors. The result of WBG is much lower channel resistances and reduced drive requirements.

Many SSR manufacturers drive their SSR power device with opto couplers consisting of an LED emitter driving a multi-diode photo-voltaic stack.

Both the LED's and photovoltaic stacks are challenged by a radiation environment. A second disadvantage of opto coupled drive is slow turn on and off response.

MDI replaces the optocoupler function with a tiny, transformer isolated RF drive signal. This solves the opto coupler problems and gives faster, more temperature stable operation, as well as excellent radiation resistance.



300V/3A Solid State Relay Model 53815 Form B Model 53814 Form A

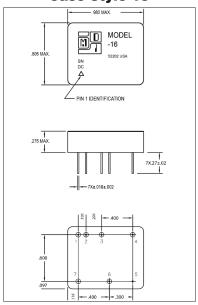
PARAMETER	CONDITION	MIN	TYP	MAX	
Contact Ratng V	Max	_	_	300V	
Contact Rating I	Max	_	_	3A	
Contact Resistance, 25°C	Energized	_	0.2 Ω	0.25Ω	
Contact Resistance, 125°C	Energized	_	0.35Ω	0.45Ω	
Leakage Current, 600V, 25°C	Off	_	_	60µA	
Leakage Current, 600V, 125°C	Off	_	_	100μΑ	
Bias Voltage	_	4.7V	5.0V	5.3V	
Bias Current	_	_	30mA	50mA	
Command Current	_	0.1mA	0.8mA	2.0mA	
Delay Time, energized	_	_	12µS	30μS	
Delay Time, de-energized	_	_	20µS	40μS	
Energize Time, dynamic	_	_	12µS	30μS	
De-edergize time, dynamic	_	_	5µS	20µS	

For Heat Removal and Mounting Recommendations See MDI application notes on mounting considerations for DC-DC Converters

53814/53815

HYBRID SOLID STATE RELAY

Case Style 16



Pin Out	Pin Out Chart				
Pin 1	Bias +5 VDC				
Pin 2	Bias Gnd				
Pin 3	Coil				
Pin 4	N/C				
Pin 5	Case				
Pin 6	Switch Positive				
Pin 7	Switch Negative				

Model No. Case Style	Pin Count	Mounting
E2011/E201E 16	7	Coam Wold Flangeless DCP Mount

GRADE LEVELS:Please specify grade level for your application. EU grade units will be shipped if no option is specified.

Engineering Units 45K, +85°C aerospace 45K, +125°C aerospace LE

S 100K+[™], +85°C space SE 100K+[™], +125°C space

